

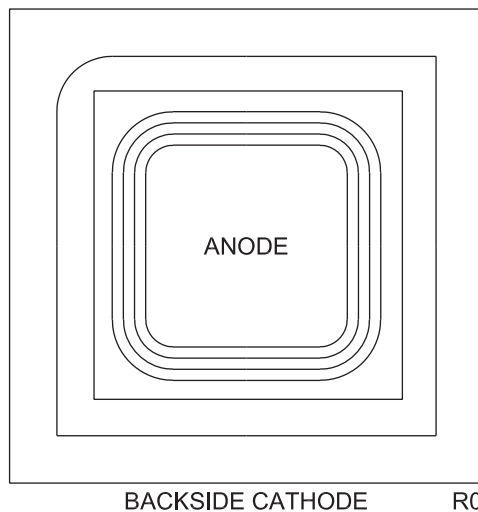
PROCESS CPD106R
Schottky Diode
Schottky Diode Chip



PROCESS DETAILS

Die Size	8.3 x 8.3 MILS
Die Thickness	3.9 MILS
Anode Bonding Pad Area	5.4 x 5.4 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



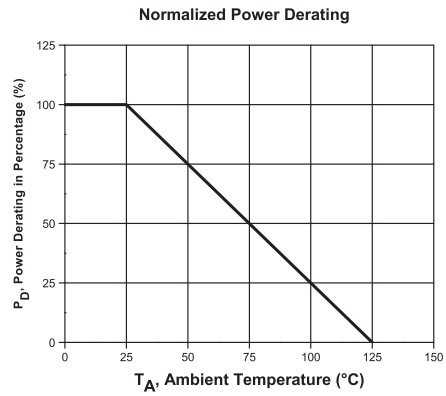
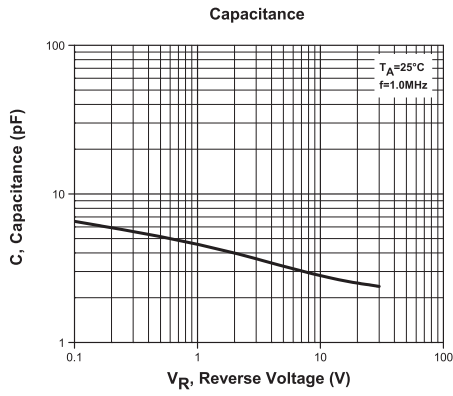
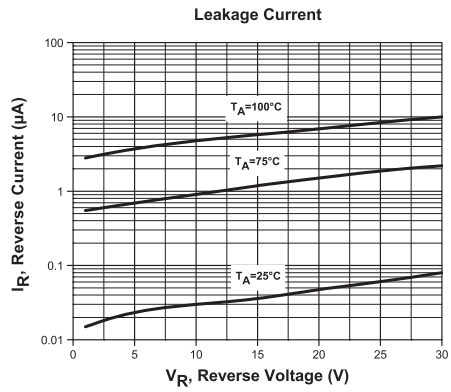
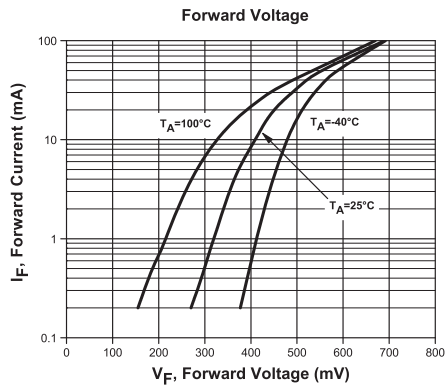
GROSS DIE PER 5 INCH WAFER
251,364

PRINCIPAL DEVICE TYPE
CTLSH01-30

R0 (20-April 2011)

PROCESS CPD106R

Typical Electrical Characteristics



R0 (20-April 2011)